IN THE SPECIFICATION:

Please amend the specification as follows:

[0030] As mentioned above, the invention forms fins for a FinFET device using sidewall image transfer processing, yet the invention eliminates the need for a separate trim mask. Instead, the invention trims the unwanted portions of the loop structure formed during the sidewall image transfer processing using the same mask that defines the source and drain contacts. The inventive methodology begins by patterning a rectangular sacrificial mandrel 10 on a hard-mask layer 16 that overlies a layer of semiconductor material 11 on a buried oxide (BOX) 13, as shown in Figure 1A and 1B. Next, the invention forms sidewall spacers 12 along the vertical surfaces of the mandrel 10. The sidewall spacers 12 are formed by depositing a masking material and then performing a selective anisotropic etching process that removes material from horizontal surfaces at substantially higher rates than it removes material from vertical surfaces. This process leaves the deposited mask material 12 only along the sides of the mandrel 10, as shown in Figures 1A. Subsequently, the mandrel 10 is removed, the hard-mask material 16 is etched using the spacers 12 as masks, and the spacers 12 are removed to leave a freestanding rectangular loop of mask material 16 having two longer sections 15 and two shorter sections 14.

[0034] Next, as shown Figure 4A, the invention forms a contact mask 40 over a portion of the conductive contact material 30 that is above source and drain regions of a first fin 42 of the two longer fins 21. The invention follows this by selectively etching regions of the conductive contact material 30 and the semiconductor material 11 that are not protected by the contact mask. Such an etch will not affect the gate 20 or spacers 31. This leaves the conductive contact material 30 only on the source and drain regions of the first fin 42 and removes source and drain regions of a second fin 41 of the two longer fins 21. Therefore, the contact mask 40 performs two functions by patterning the source and drain contacts and by trimming the unwanted portion of the semiconductor material 11. By utilizing the contact mask-44 40 in this manner, the invention avoids the need for a separate trim mask.